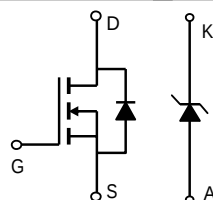
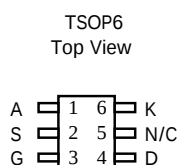


AO6706
**N-Channel Enhancement Mode Field Effect Transistor
with Schottky Diode**
General Description

The AO6706 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. A Schottky diode is provided to facilitate the implementation of a bidirectional blocking switch, or for DC-DC conversion applications. Standard Product AO6706 is Pb-free (meets ROHS & Sony 259 specifications). AO6706L is a Green Product ordering option. AO6706 and AO6706L are electrically identical.

Features

$V_{DS} (V) = 30V$
 $I_D = 3.6A (V_{GS} = 10V)$
 $R_{DS(ON)} < 65m\Omega (V_{GS} = 10V)$
 $R_{DS(ON)} < 75m\Omega (V_{GS} = 4.5V)$
 $R_{DS(ON)} < 160m\Omega (V_{GS} = 2.5V)$
SCHOTTKY
 $V_{DS} (V) = 20V, I_F = 1A, V_F < 0.5V @ 0.5A$


Absolute Maximum Ratings $T_A = 25^\circ C$ unless otherwise noted

Parameter	Symbol	MOSFET	Schottky	Units
Drain-Source Voltage	V_{DS}	30		V
Gate-Source Voltage	V_{GS}	± 12		V
Continuous Drain Current ^A	$T_A = 25^\circ C$	I_D	3.3	A
	$T_A = 70^\circ C$		2.6	
Pulsed Drain Current ^B	I_{DM}	10		
Schottky reverse voltage	V_{KA}		20	V
Continuous Forward Current ^A	$T_A = 25^\circ C$	I_F	2	A
	$T_A = 70^\circ C$		1	
Pulsed Forward Current ^B	I_{FM}		10	
Power Dissipation	$T_A = 25^\circ C$	P_D	1.15	W
	$T_A = 70^\circ C$		0.7	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	-55 to 150	$^\circ C$

Parameter: Thermal Characteristics MOSFET		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	t ≤ 10s	R _{θJA}	80.3	110	°C/W
Maximum Junction-to-Ambient ^A	Steady-State		117	150	
Maximum Junction-to-Lead ^C	Steady-State	R _{θJL}	43	80	
Thermal Characteristics Schottky					
Maximum Junction-to-Ambient ^A	t ≤ 10s	R _{θJA}	109.4	135	°C/W
Maximum Junction-to-Ambient ^A	Steady-State		136.5	175	
Maximum Junction-to-Lead ^C	Steady-State	R _{θJL}	58.5	80	

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =24V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±12V			100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1	1.4	1.8	V
I _{D(ON)}	On state drain current	V _{GS} =4.5V, V _{DS} =5V	10			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =3.3A T _J =125°C		44 64	65 90	mΩ
		V _{GS} =4.5V, I _D =3.0A		53	75	mΩ
		V _{GS} =2.5V, I _D =1A		106	160	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =3.3A		11.7		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.81	1	V
I _S	Maximum Body-Diode Continuous Current				2.5	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, f=1MHz		226	270	pF
C _{oss}	Output Capacitance			39		pF
C _{rss}	Reverse Transfer Capacitance			29		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		1.4	1.7	Ω
SWITCHING PARAMETERS						
Q _g	Total Gate Charge	V _{GS} =4.5V, V _{DS} =15V, I _D =3.3A		3	3.6	nC
Q _{gs}	Gate Source Charge			1.4		nC
Q _{gd}	Gate Drain Charge			0.55		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =15V, R _L =4.7Ω, R _{GEN} =6Ω		2.6		ns
t _r	Turn-On Rise Time			3.2		ns
t _{D(off)}	Turn-Off DelayTime			14.5		ns
t _f	Turn-Off Fall Time			2.1		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =3.3A, di/dt=100A/μs		10.2	13	ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =3.3A, di/dt=100A/μs		3.8		nC
SCHOTTKY PARAMETERS						
V _F	Forward Voltage Drop	I _F =0.5A		0.39	0.5	V
I _{rm}	Maximum reverse leakage current	V _R =16V V _R =16V, T _J =125°C			0.1 20	mA
C _T	Junction Capacitance	V _R =10V		34		pF
t _{rr}	Schottky Reverse Recovery Time	I _F =1A, di/dt=100A/μs		5.2	10	ns
Q _{rr}	Schottky Reverse Recovery Charge	I _F =1A, di/dt=100A/μs		0.8		nC

A: The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design. The current rating is based on the t ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using 80μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

Rev2: August 2005

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

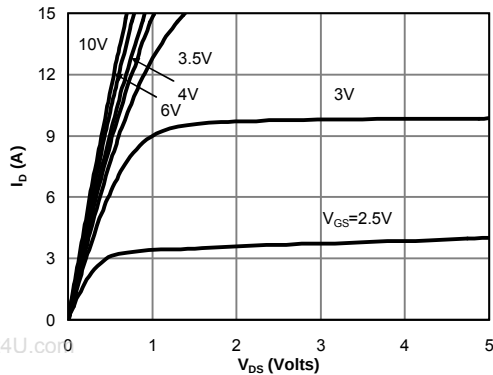


Fig 1: On-Region Characteristics

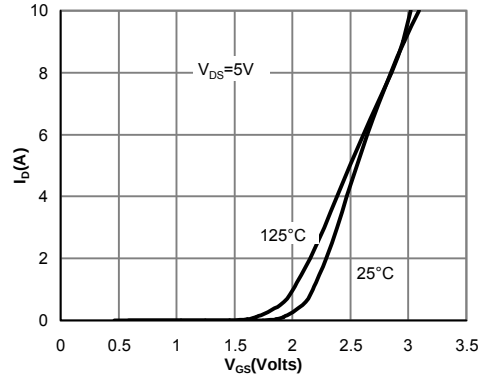


Figure 2: Transfer Characteristics

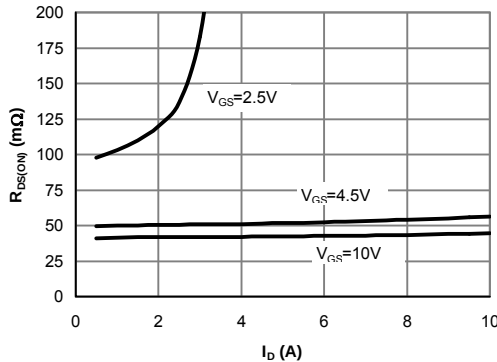


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

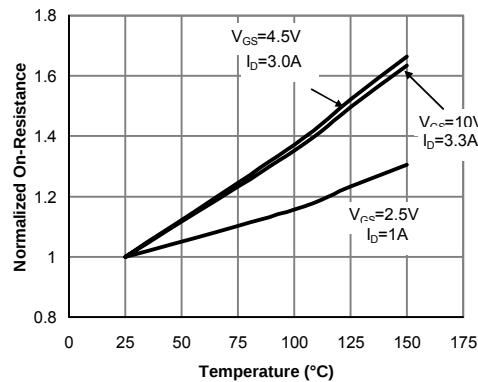


Figure 4: On-Resistance vs. Junction Temperature

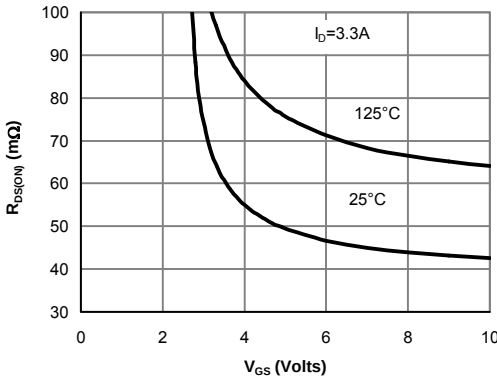


Figure 5: On-Resistance vs. Gate-Source Voltage

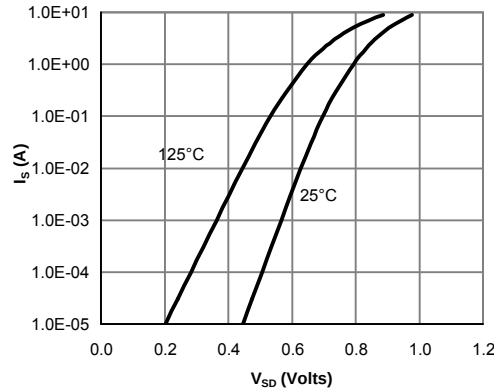


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

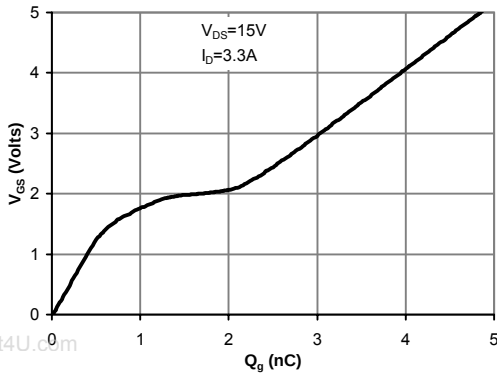


Figure 7: Gate-Charge Characteristics

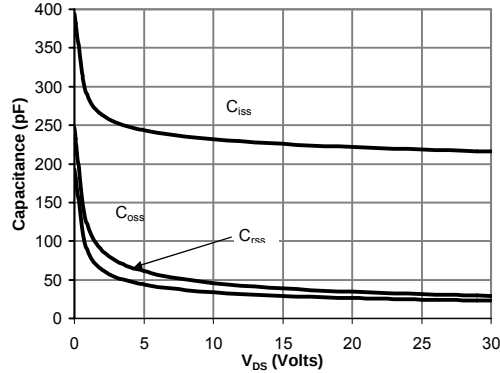


Figure 8: Capacitance Characteristics

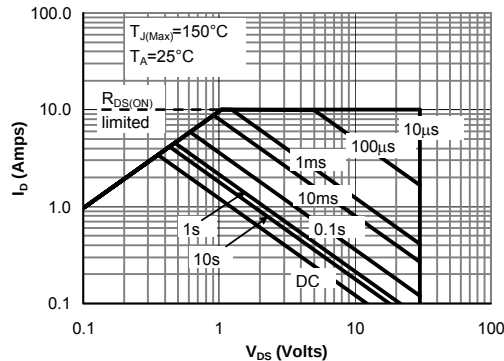


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

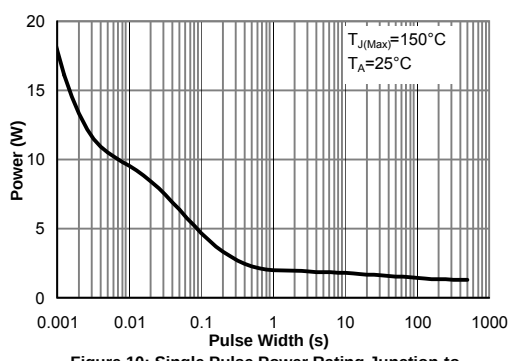


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

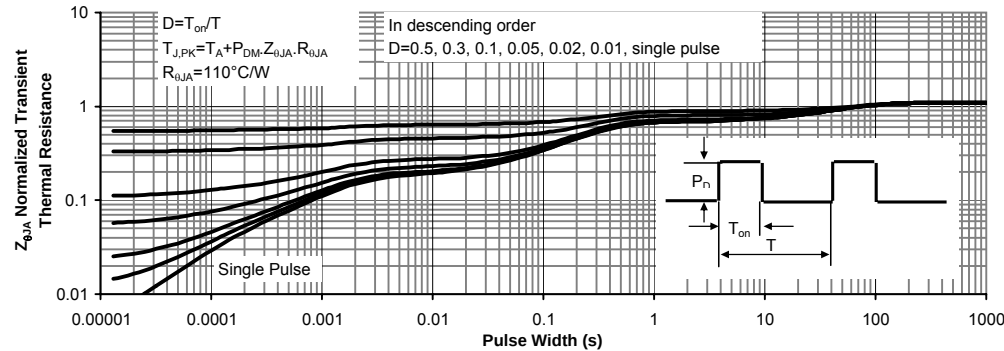


Figure 11: Normalized Maximum Transient Thermal Impedance